

# *Facile synthesis of high-quality graphene nanoribbons*

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## *graphene*

- highest carrier mobility
- lowest dimensionality
- highest mechanical stability
- easiest system to understand the band structure

## *proposed uses*

- alternative for Si in semiconductors FETs
- solar energy harvesting
- catalysis in fuel cells
- band controllable systems in optical detection
- high frequency detectors in the range of T Hz
- spin transport

## *issues*

- not any easy method to tune the band gap
- difficult to have any well defined pattern as the growth is self governed
- proposed spin properties can be possible only with well well defined edge structures

## *background*

- graphene nanoribbons - spin transport properties & tuneable band gap
- lithographic, chemical and sonochemical methods
- recently unzipping of MWNTs by a few chemical steps
- but heavily oxidised and defective nanoribbons
- masked gas-phase plasma etching of MWNTs -limited to the nanoribbons on substrate
- catalytic cutting and high current pulse burning - quality and quantity is limited.

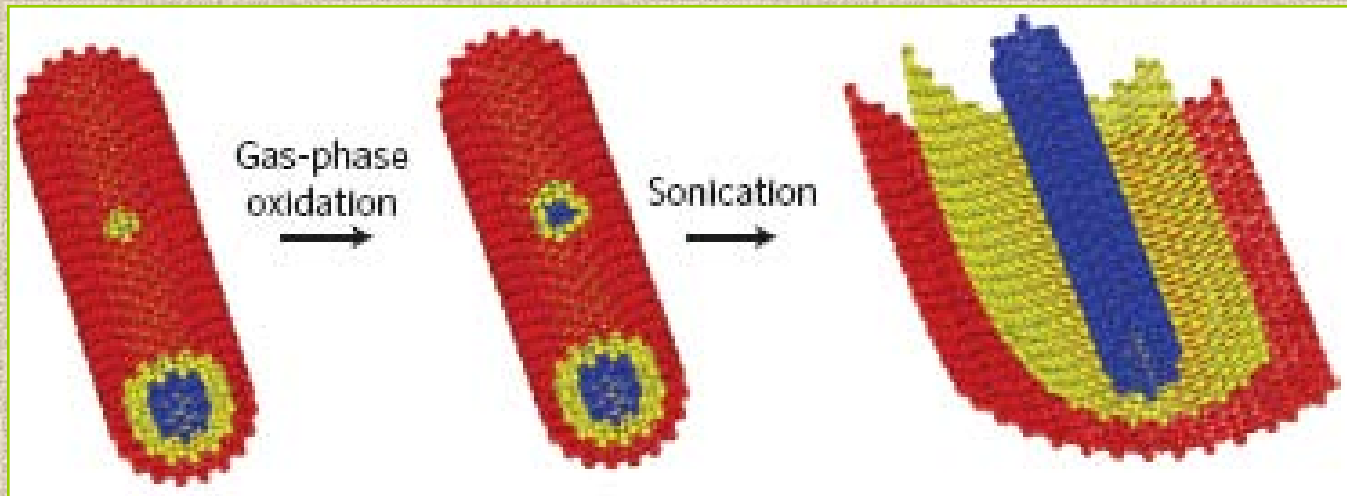
## *present work*

- pristine nanoribbons by unzipping MWNTs using mechanical sonication in organic solvents
- high quality ribbons with smooth edges and small  $I(D)/I(G)$
- highest electrical conductance and highest mobility ( $1500 \text{ cm}^2/\text{Vs}$ )
- at low temperatures show phase coherent transport and Fabry-Perote interference suggesting minimal defects and edge smoothness
- yield is 2 % from the raw soot arc discharge

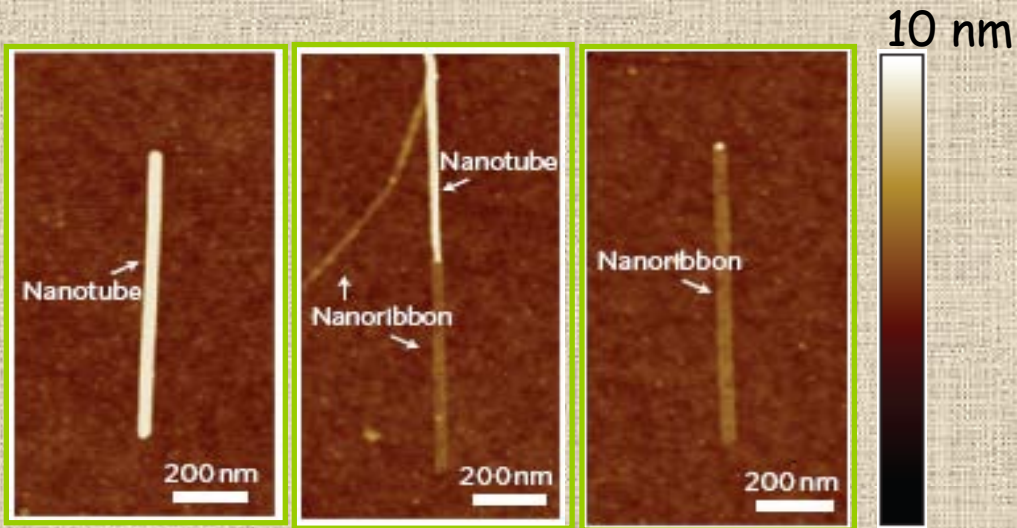


## *method of preparation*

- raw soot from arc discharge which contains MWNTs were calcined in air at 500 °C - mild step which etches / oxidises only the defect site or ends
- dispersed in 1, 2 -dichloroethane organic solution of poly(*m*-phenylenevinylene-co-2,5-dioxy-*p*-phenylenevinylene) and sonicated
- ultracentrifuged to remove CNTs and graphitic waste to form 60% GNRs in supernatant.



# Atomic Force Micrograms

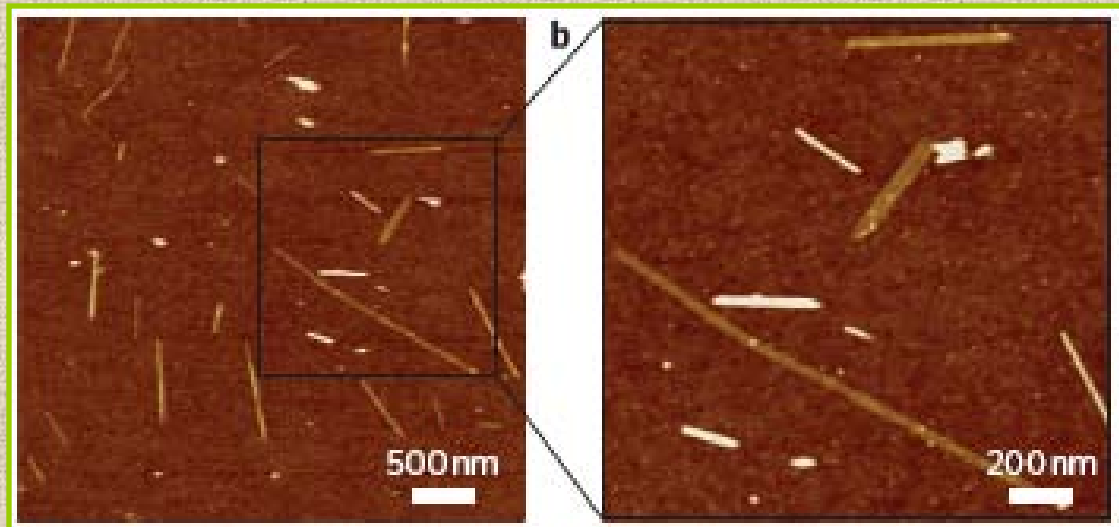


9 nm

1.4 nm

1.6 nm

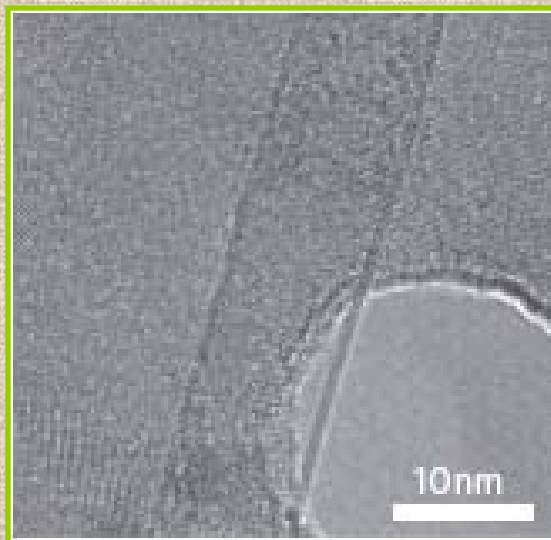
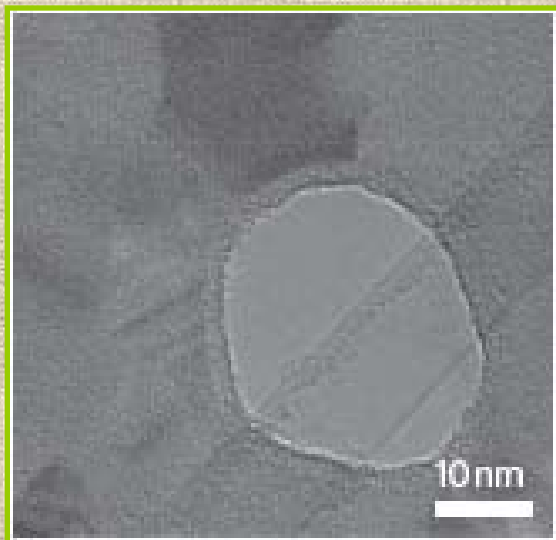
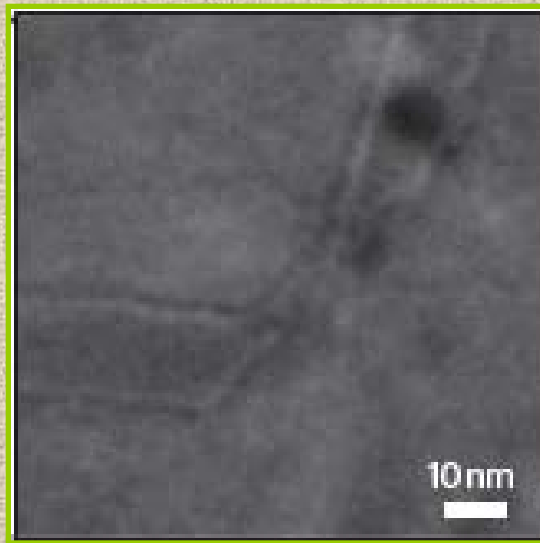
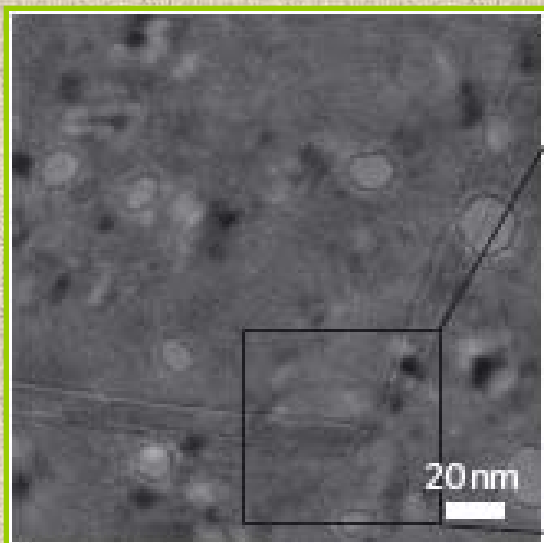
1.8 nm, 18 nm  
1.4 nm, 48 nm  
1.4 nm, 22 nm



# Transmission Electron Microgram

12 nm GNR  
With a kink  
due to folding

200 kV  
Porous silicon  
grid



10 & 12 nm GNR

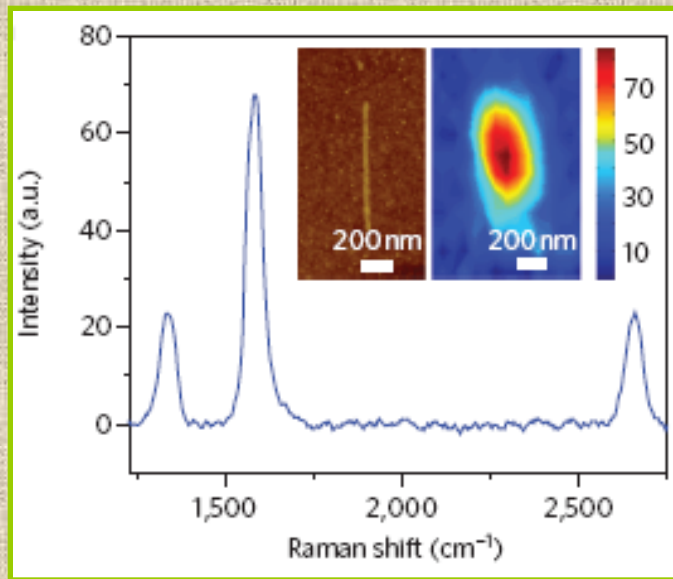
PmPV - attached

120 kV

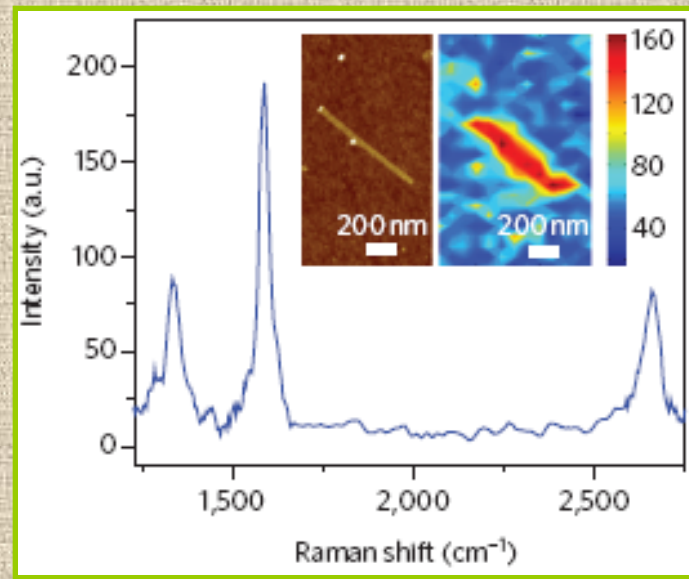


- no defects were created
- while calcination existing defects form etch pits and while sonication they get unzipped into GNRs
- the number of layers depend on the depth of etch pits forming single, bi and trilayer
- low oxidation was proved by low I(D) & XPS O1s was comparable to that of the MWNTs
- Sonochemistry and hot gas bubbles created during sonication causes the unzipping which proceeds along the tube axis
- resulting nanoribbons were seperated from the inner tubes and the edges were functionalised noncovalently by pi-stacking using PmPVs
- applicable to CVD grown MWNTs too

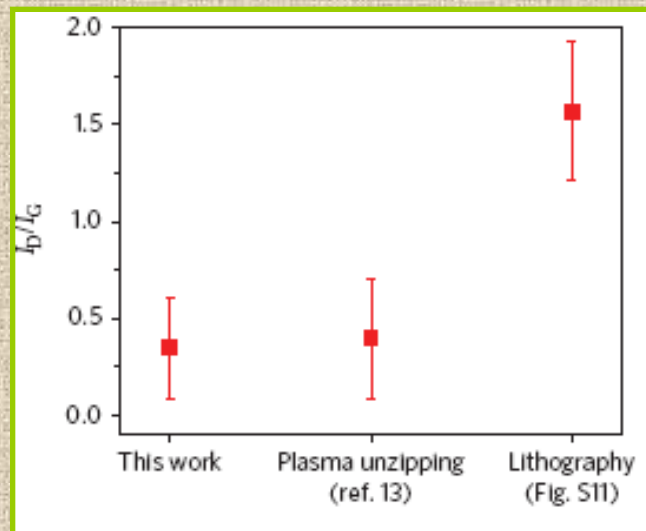
# Inelastic Raman scattering



1.5 nm, 20 nm  
 $I_D/I_G = 0.3$   
bi layer



1.8 nm, 20 nm  
 $I_D/I_G = 0.5$   
tri layer

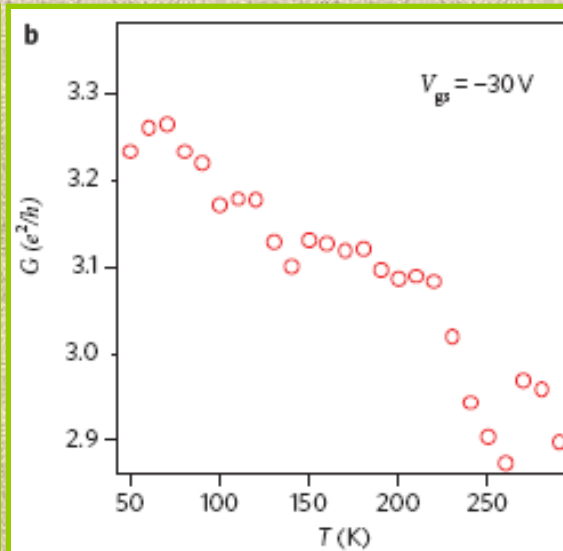
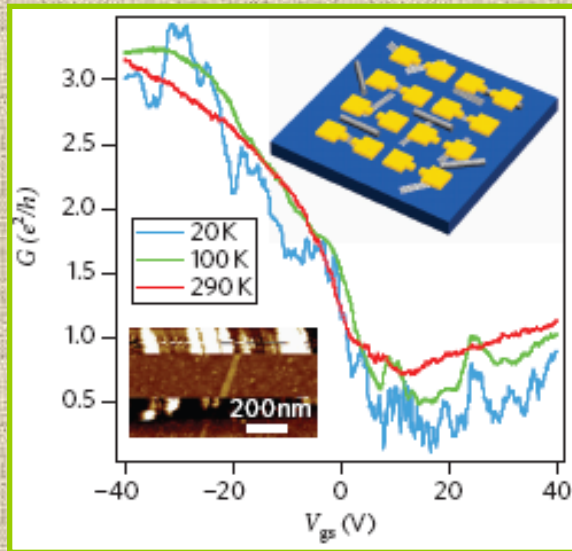


bi layer  
average of 15 GNRs  
of 20 nm width

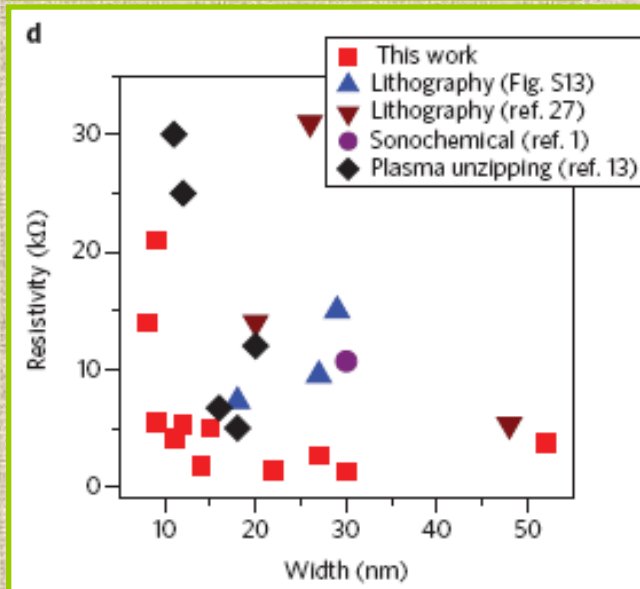
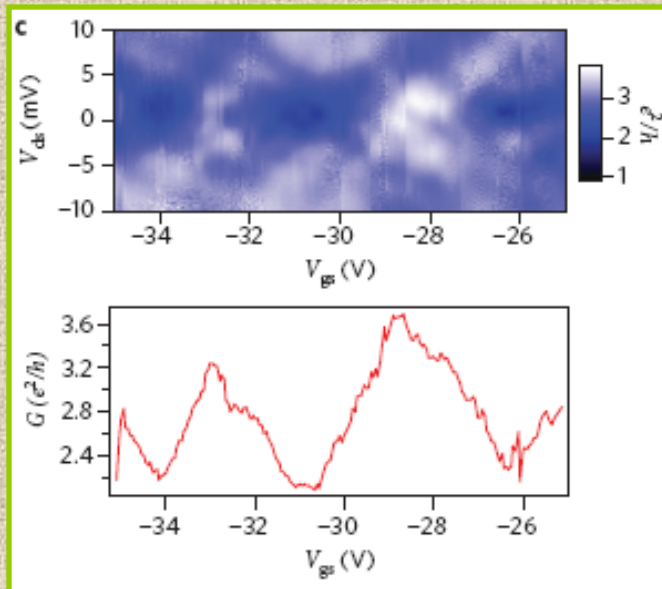


# Electrical characterisation

p channel conductivity increases with decrease in temperature



14 nm  
1500  $\text{cm}^2/\text{Vs}$



the bandgap of the nanoribbon was estimated to be  $E_g \approx 10\text{-}15$  meV by fitting the temperature dependence of minimum conductance to thermal activation over a barrier of  $E_g/2$

## *conclusions*

- prepared high quality GNRs of various widths 10-30 nm by mild gas-phase etching followed by sonication
- Imaged using AFM, TEM and Raman
- Transport measurements were done which shows high mobility and high conductivity
- obtained highest mobility and lowest resistivity for GNRs
- metallic behavior of the valence band along with reduced phonon scattering at low temperatures
- Fabrey-perpt lilke conductivity characteristics suggests that the GNRs are of high quality with well defined edges

*thank you all*